Discrete POWER & Signal **Technologies** 

# MPSL01

FAIRCHILD SEMICONDUCTOR TM

## MPSL01



## **NPN General Purpose Amplifier**

This device is designed for general purpose, high voltage amplifiers and gas discharge display driving. Sourced from Process 16. See 2N5551 for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	120	V	
V <sub>CBO</sub>	Collector-Base Voltage	140	V	
$V_{\text{EBO}}$	Emitter-Base Voltage	5.0	V	
I <sub>C</sub>	Collector Current - Continuous	200	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics

Thermal Characteristics     TA = 25°C unless otherwise noted				
Symbol	Characteristic	Max	Units	
		MPSL01		
P <sub>D</sub>	Total Device Dissipation Derate above 25℃	625 5.0	mW mW/∘C	
$R_{\theta_{JC}}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	200	°C/W	

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## NPN General Purpose Amplifie

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Symbol	Parameter	Test Conditions	Min	Max	Units
···					
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 {\rm mA}, \ I_{\rm B} = 0$	120		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, I_{E} = 0$	140		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 75 \text{ V}, I_E = 0$		1.0	μA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		100	nA
				• •	-
ON CHAF	RACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	50	300	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		0.2	V
		$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		0.3	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		1.2	V
		$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		1.4	V

C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		8.0	pF
h <sub>fe</sub>	Small-Signal Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	30		
FT	Current Gain - Bandwidth Product	$I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 10 \text{ V},$	60		MHz

\*Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%



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